



DMN3300U

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Package	I _D T _A = +25°C	
	0.15Ω @ $V_{GS} = 4.5V$		2A	
30V	0.2Ω @ $V_{GS} = 2.5V$	SOT23	1.6A	
300	0.25Ω @ $V_{GS} = 1.8V$	30123	1.4A	
	0.3Ω @ V _{GS} = 1.5V		1.2A	

Description

This new generation MOSFET has been designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

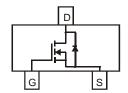
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (approximate)

SOT23



Top View



Internal Schematic

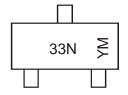
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3300U-7	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



33N = Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	201	1 20)12	201	3	2014	2015	2016	2017
Code	U	V	W	Х	Y		Z	Α		В	С	D	Е
Month	Jan	Feb	Mar	Apr	Мау	Jun	Ju	ıl	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7		8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	30	V		
Gate-Source Voltage	V_{GSS}	±12	V		
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	Ι _D	1.5 1.2	А
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	2.0 1.6	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	8	Α		
Maximum Body Diode Continuous Current (Note 6)	Is	1.6	Α		

Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	ר	0.7	W	
Total Fower Dissipation	(Note 6)	P_{D}	1.3	VV	
Thermal Resistance, Junction to Ambient	(Note 5)	2	176		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	102	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	$R_{ heta JC}$	45		
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

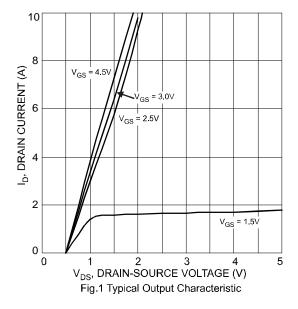
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			_			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	37		V	$V_{GS} = 0V, I_D = 100 \mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_		1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	IGSS	_	_	±10	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)	•					
Gate Threshold Voltage	V _{GS(th)}	0.5		1	>	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
			100 140 185 240	150 200 250 300		$V_{GS} = 4.5V, I_D = 4.5A$
Static Drain-Source On-Resistance	D	_			mΩ	$V_{GS} = 2.5V, I_D = 3.5A$
Static Dialii-Source Off-Resistance	R _{DS} (ON)					$V_{GS} = 1.8V, I_D = 1.5A$
						$V_{GS} = 1.5V, I_D = 0.5A$
Forward Transfer Admittance	Y _{fs}	_	5	_	S	$V_{DS} = 5V, I_D = 2.4A$
Diode Forward Voltage	V_{SD}	_	0.8	1.1	V	$V_{GS} = 0V, I = 0.5A$
DYNAMIC CHARACTERISTICS (Note 8)	•					
Input Capacitance	C _{iss}	_	193		pF	10/1/1/
Output Capacitance	Coss	_	35		pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	23	_	pF	1 = 1.0IVID2
Turn-On Delay Time	t _{d(on)}	_	7			
Rise Time	tr		24		ns	$V_{DD} = 10V$, $R_L = 10\Omega$
Turn-Off Delay Time	t _{d(off)}		24		115	$I_D = 1A$, $V_{GEN} = 4.5V$, $R_G = 6\Omega$
Fall Time	t _f		12	_		

Notes:

- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
 Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing





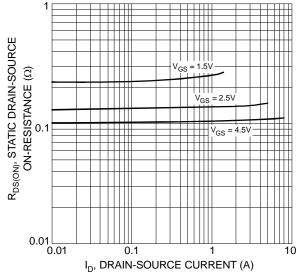
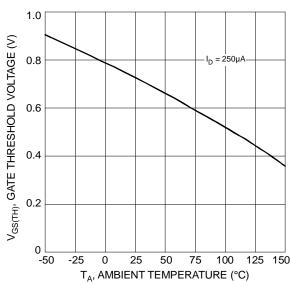
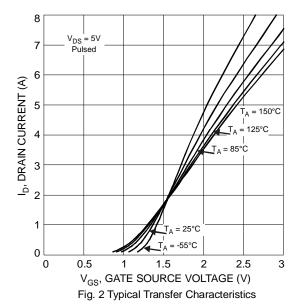


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage







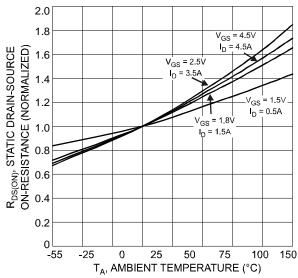
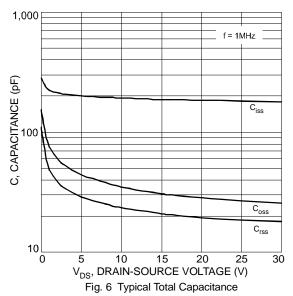
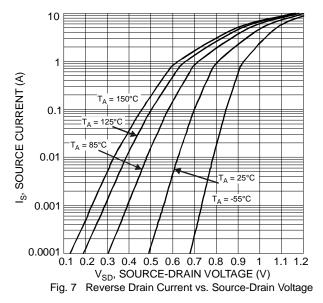
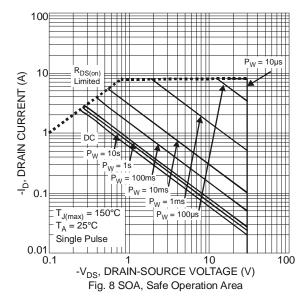


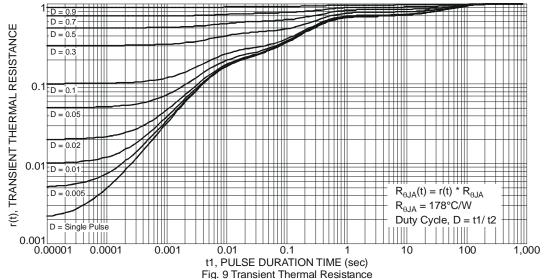
Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature





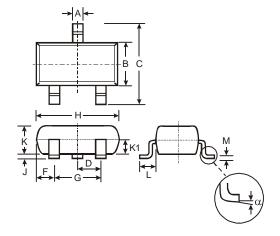






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

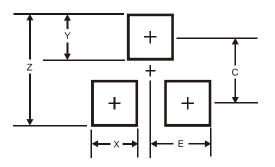


	SOT23								
Dim	Min	Max	Тур						
Α	0.37	0.51	0.40						
В	1.20	1.40	1.30						
С	2.30	2.50	2.40						
D	0.89	1.03	0.915						
F	0.45	0.60	0.535						
G	1.78	2.05	1.83						
Н	2.80	3.00	2.90						
J	0.013	0.10	0.05						
K	0.903	1.10	1.00						
K1	-	1	0.400						
L	0.45	0.61	0.55						
М	0.085	0.18	0.11						
α	0°	8°	-						
All	All Dimensions in mm								



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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